

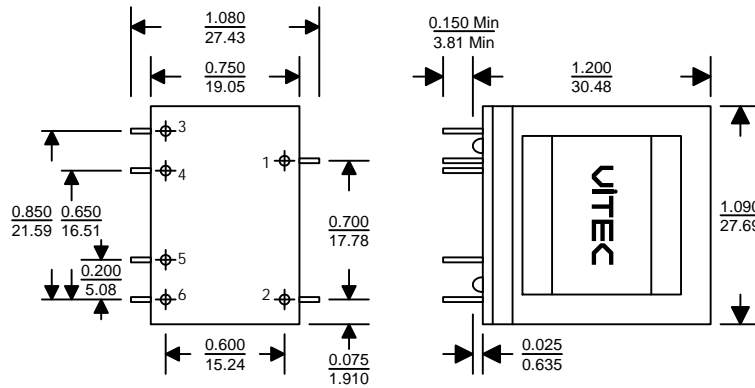
TYPE 56P

MOSFET GATE DRIVE TRANSFORMER

FEATURES

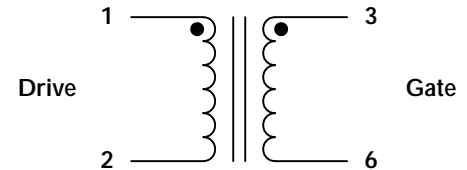
- Designed for operating frequency in excess of 200KHz.
- Low leakage inductance: drives most power FETS.
- Drive directly from pulse modulators.
- 3750 Vrms gate to drive hipot test.
- Base material meets flammability requirement of UL94V-0.
- Manufactured to UL recognized 130 insulation system.
UL file# E107307.

DRAWING

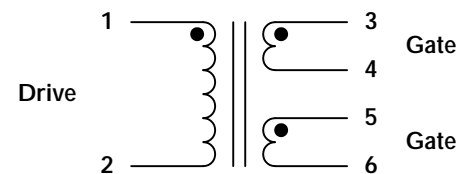


Drawing NOT to Scale

SCHEMATIC 1



SCHEMATIC 2



ELECTRICAL CHARACTERISTICS @ +25°C

Part Number	Turns Ratio +/- 5%	Lp Term 1-2	LL	DCR Drive Winding	DCR Gate Winding	Cww Drive To Gate	Cww Gate To Gate	Drive Excitation Unipolar	Drive Excitation Bipolar	Secondary RMS	Schem.
		mH	mH	Ohm	Ohm	pF	pF	V-uSec	V-uSec	mAmp	
		MIN	MAX	MAX	MAX	MAX	MAX	NOM	NOM	NOM	
56P3385	1:1	1.50	4.00	0.40	0.75	50	130	375	750	500	1
56P3386	1:1.5	1.50	4.00	0.40	2.50	50	130	375	750	200	1
56P3387	1:1:1	1.50	4.00	0.40	0.75	50	130	375	750	500	2
56P3388	1:1.5:1.5	1.50	4.00	0.40	2.50	50	130	375	750	200	2

DIELECTRIC STRENGTH

Test Between	Gate - Drive	Gate - Gate	Gate - Core	Drive - Core
RMS Test Volts 60Hz, 1 min Hold	3750	1500	2000	1750